Ordering number: EN 2746
查询2SK1065供应商

SANYO

No.2746

2SK1065

N-Channel Junction Silicon FET

High-Frequency General-Purpose Amp Applications

Features

- Very small-sized package permitting 2SK1065-applied sets to be made smaller and slimmer
- Small c_{rss} (c_{rss} = 0.04pF typ)

Absolute Maximum Ratings at Ta = 25°C

			unit
Gate to Drain Voltage	V_{GDO}	−20	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 to +150	°C

Electrical Characteristics at Ta = 25°C

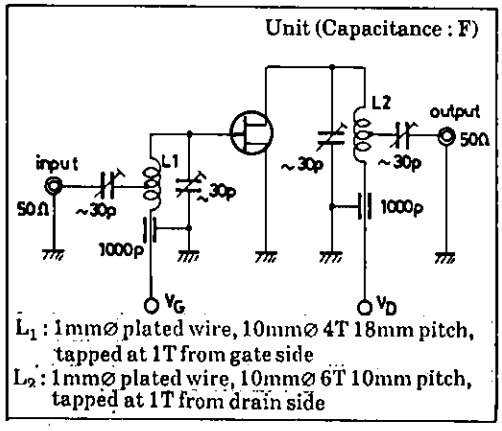
			min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDO}$	I_G = −10μA	−20			V
Gate Cutoff Current	I_{GSS}	V_{GS} = −0.5V, V_{DS} = 0			−10	nA
Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 5V, I_D = 10μA	−0.4	−1.3	−2.5	V
Drain Current	I_{DSS}	V_{DS} = 5V, V_{GS} = 0	※1.2		※12.0	mA
Forward Transfer Admittance	$\|y_{fs}\|(1)$	V_{DS} = 5V, V_{GS} = 0, f = 1kHz	2.4	6.0		mS
	$\|y_{fs}\|(2)$	V_{DS} = 5V, V_{GS} = 0, f = 100MHz	2.4	6.0		mS
Input Capacitance	c_{iss}	V_{DS} = 5V, V_{GS} = 0, f = 1MHz		4.0		pF
Reverse Transfer Capacitance	c_{rss}	V_{DS} = 5V, V_{GS} = 0, f = 1MHz		0.04	0.15	pF
Output Capacitance	c_{oss}	V_{DS} = 5V, V_{GS} = 0, f = 1MHz		4.0		pF
Power Gain	PG	V_{DS} = 5V, V_{GS} = 0, f = 100MHz		24		dB
		See specified Test Circuit.				
Noise Figure	NF	See specified Test Circuit.		3.5	6.0	dB

※ : The 2SK1065 is classified by I_{DSS} as follows (unit : mA) :

1.2 3 3.0	2.5 4 6.0	5.0 5 12.0

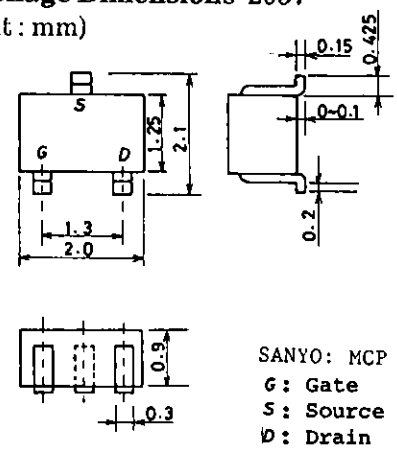
(Note) Marking : T
I_{DSS} rank : 3,4,5
●For CP package version, use the 2SK242.

PG, NF Test Circuit



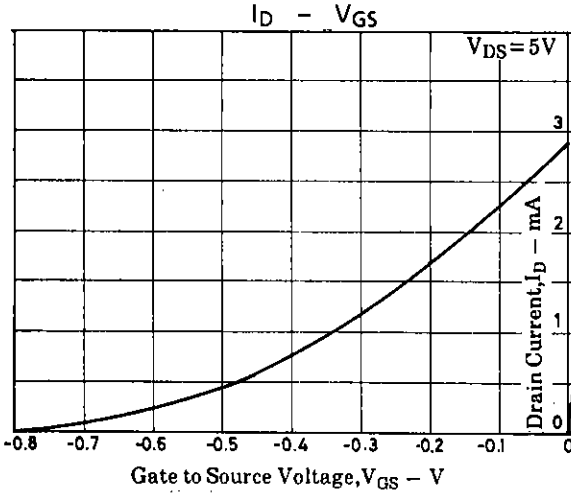
L_1 : 1mmØ plated wire, 10mmØ 4T 18mm pitch, tapped at 1T from gate side
L_2 : 1mmØ plated wire, 10mmØ 6T 10mm pitch, tapped at 1T from drain side

Package Dimensions 2057
(unit : mm)

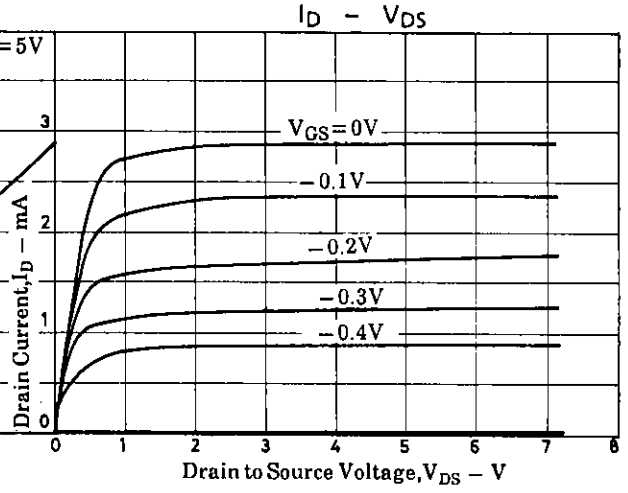


SANYO : MCP
G : Gate
S : Source
D : Drain

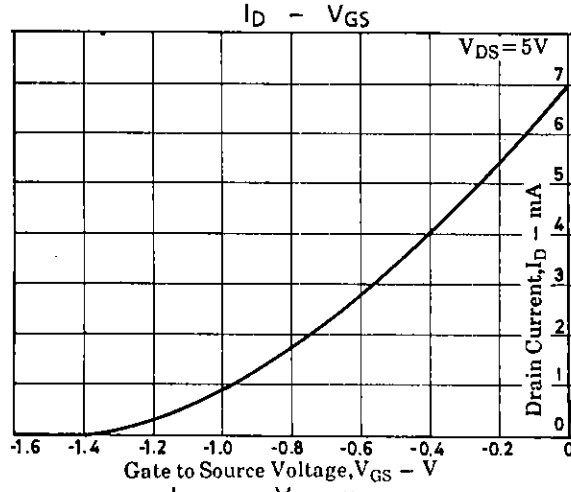
I_D – V_{GS}



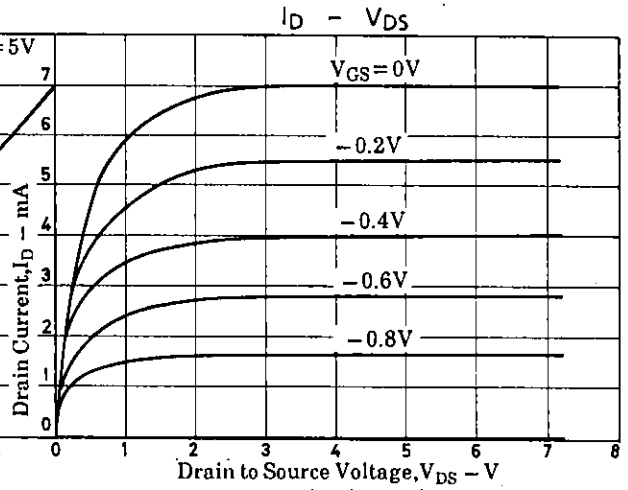
I_D – V_{DS}



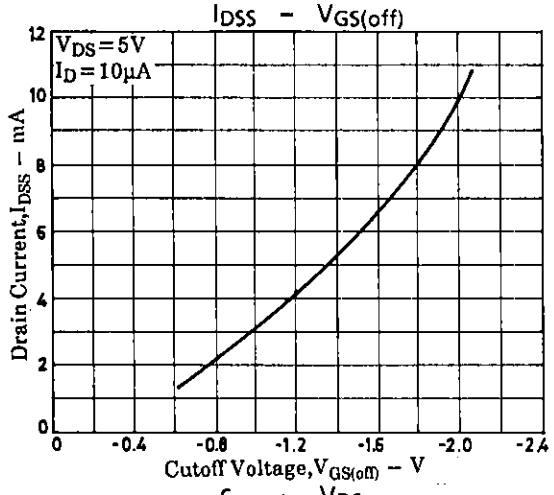
I_D – V_{GS}



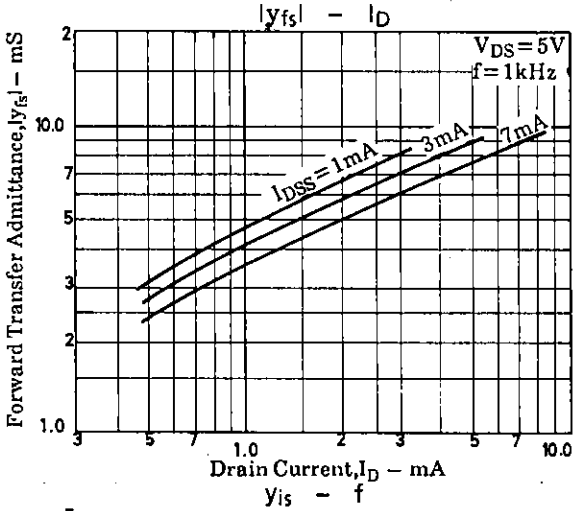
I_D – V_{DS}



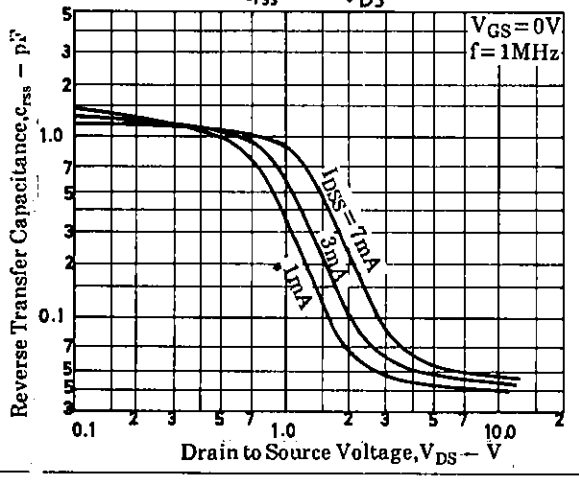
I_{DSS} – $V_{GS(off)}$



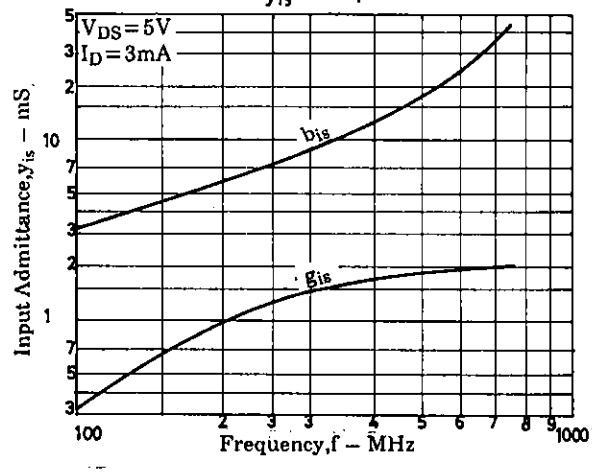
$|y_{fs}|$ – I_D



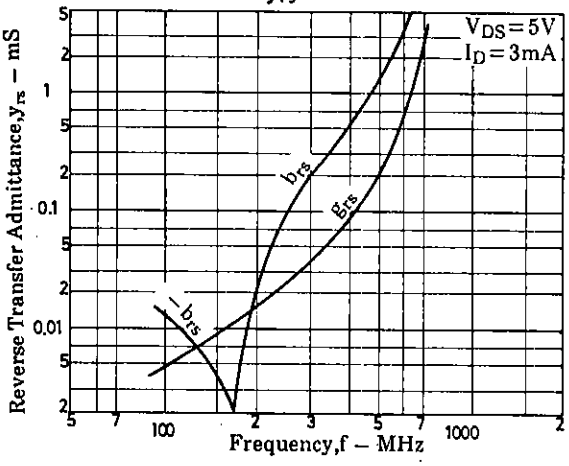
C_{rss} – V_{DS}



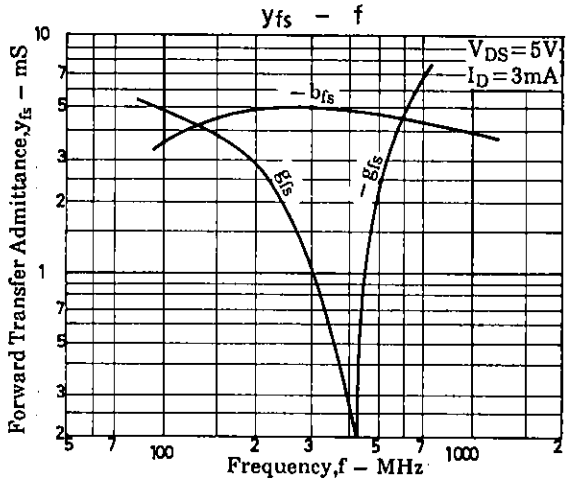
y_{is} – f



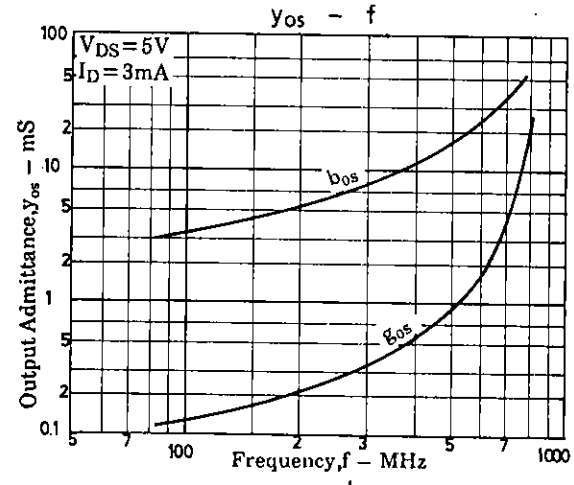
y_{rs} – f



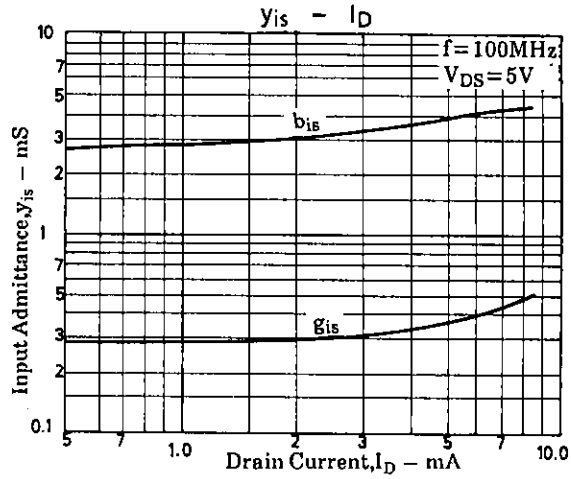
y_{fs} – f



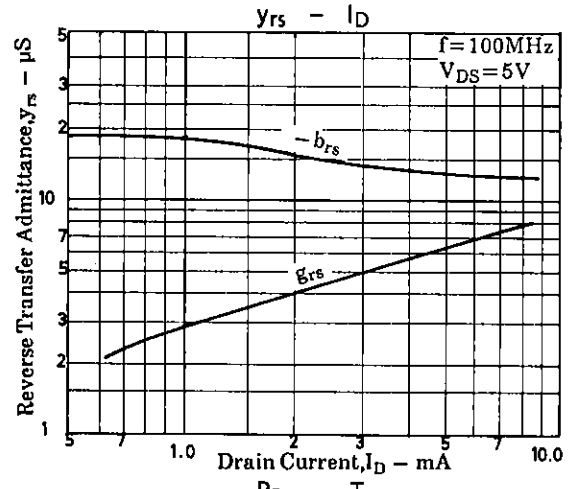
y_{os} – f



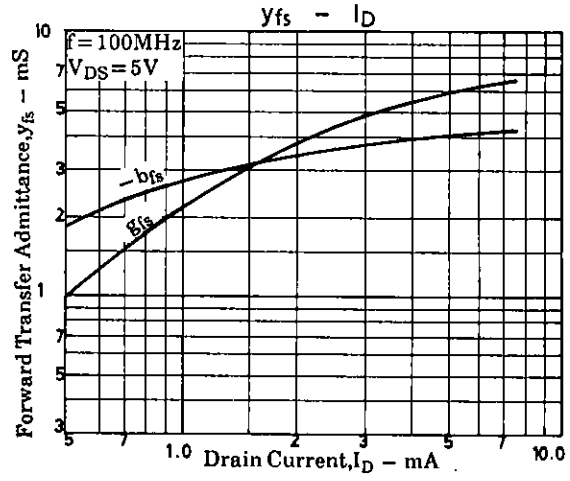
y_{is} – I_D



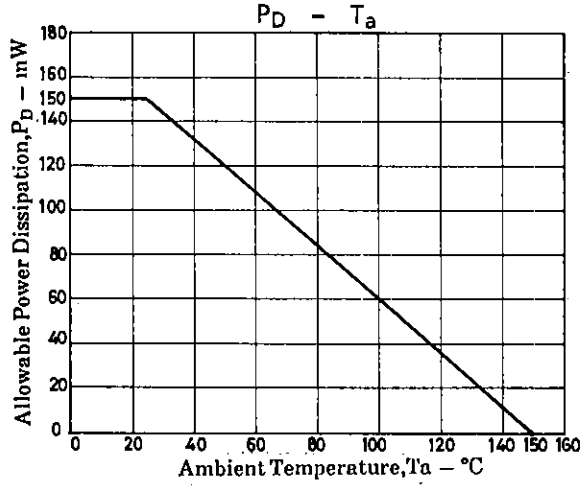
y_{rs} – I_D



y_{fs} – I_D



P_D – T_a



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